

IR-Si311 Emitter Datasheet

The IR-Si series emitters are designed to supply higher temperatures and greater output compared to other IR sources. The patented silicon nitride or silicon carbide material ensures a robust design.

Recommended (Maximum) Operating Parameters

Voltage, V	12	(14)
Temperature °C	1025	(1090)
Current, A	5.2	(5.5)
Power, W	62.4	(77)

Properties at Recommended Parameters

Life	5000+ Hours
Emissivity, %	80
Active Area (mm)	4.5(D) X 17(L)
Material	Silicon Nitride

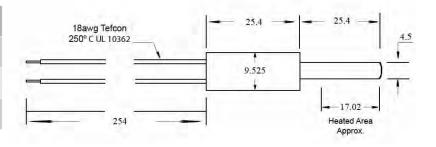
IR-Si series emitters can be paired with elliptical or parabolic reflectors for a significantly more efficient collimation of energy. Windows are also available for specific transmitting ranges.

<u>Contact Information:</u> Boston Electronics www.boselec.com shop.boselec.com boselec@boselec.com +1.617.566.3821



BostonElectronics

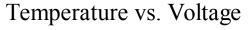
Note: all dimensions in mm



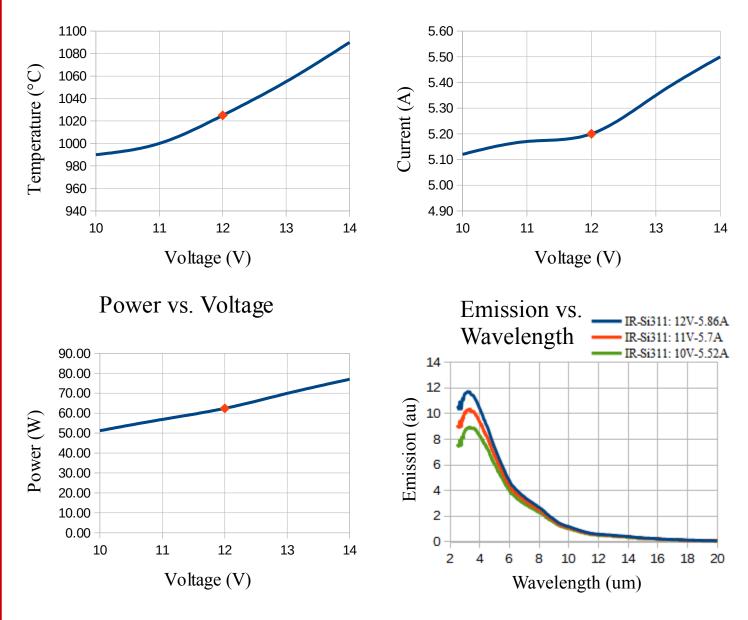
Sample Data Points

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V	10	11	12	13	14
А	5.12	5.17	5.20	5.35	5.5
W	51.20	56.87	62.40	69.91	77
°C	990	1000	1025	1055	1090



Current vs. Voltage



Published June 4, 2014. Specifications subject to change without notice. Please visit our website for the most up to date information.